### NUP6012PMU

# **Six-Line Transient Voltage Suppressor Array**

## ESD Protection Diodes with Ultra-Low (0.7 pF) Capacitance

The six-line voltage transient suppressor array is designed to protect voltage-sensitive components that require ultra-low capacitance from ESD and transient voltage events. This device features a common anode design which protects six independent high speed data lines in a single six-lead UDFN low profile package.

Excellent clamping capability, low capacitance, low leakage, and fast response time make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, it is suited for use in high frequency designs.

#### **Features**

- Low Capacitance Data Lines (0.7 pF Typical)
- Protects up to Six Data Lines
- UDFN Package, 1.6 x 1.6 mm
- Low Profile of 0.50 mm for Ultra Slim Design
- ESD Rating: IEC61000-4-2: Level 4
  - Contact (14 kV)
- $D_1$ ,  $D_2$ ,  $D_3$ ,  $D_4$ ,  $D_5$  and  $D_6$  Pins = 5.2 V Minimum Protection
- RoHS Compliant
- This is a Pb-Free Device

#### **Typical Applications**

- USB 2.0 High-Speed Interface
- Cell Phones
- MP3 Players
- SIM Card Protection

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C, unless otherwise specified)

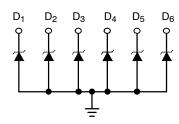
Symbol	Rating	Value	Unit
$T_J$	Operating Junction Temperature Range	-40 to 125	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
TL	Lead Solder Temperature – Maximum (10 seconds)	260	°C
ESD	IEC 61000-4-2 Contact	14000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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#### MARKING DIAGRAM



UDFN6 1.6x1.6 MU SUFFIX CASE 517AP



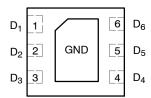
XX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

#### **PIN CONNECTIONS**



#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NUP6012PMUTAG	UDFN6 (Pb-Free)	3000/Tape & Reel

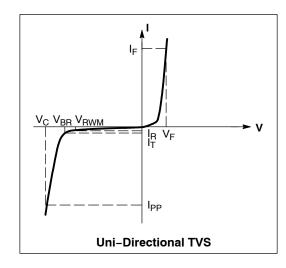
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### NUP6012PMU

#### **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
$V_{RWM}$	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
l <sub>F</sub>	Forward Current
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>
P <sub>pk</sub>	Peak Power Dissipation
С	Max. Capacitance @ V <sub>R</sub> = 0 and f = 1.0 MHz



#### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C, unless otherwise specified)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Reverse Working Voltage (D <sub>1</sub> , D <sub>2</sub> , D <sub>3</sub> , D <sub>4</sub> , D <sub>5</sub> and D <sub>6</sub> )	(Note 1)	$V_{RWM}$	-	-	4.0	V
Breakdown Voltage (D <sub>1</sub> , D <sub>2</sub> , D <sub>3</sub> , D <sub>4</sub> , D <sub>5</sub> and D <sub>6</sub> )	I <sub>T</sub> = 1 mA, (Note 2)	$V_{BR}$	5.2	5.5	_	V
Reverse Leakage Current (D <sub>1</sub> , D <sub>2</sub> , D <sub>3</sub> , D <sub>4</sub> , D <sub>5</sub> and D <sub>6</sub> )	@ V <sub>RWM</sub>	I <sub>R</sub>	-	-	1.0	μΑ
Capacitance (D <sub>1</sub> , D <sub>2</sub> , D <sub>3</sub> , D <sub>4</sub> , D <sub>5</sub> and D <sub>6</sub> )	V <sub>R</sub> = 0 V, f = 1 MHz (Line to GND)	СЈ	_	0.7	0.9	pF

TVS devices are normally selected according to the working peak reverse voltage (V<sub>RWM</sub>), which should be equal or greater than the DC or continuous peak operating voltage level.

<sup>2.</sup>  $V_{BR}$  is measured at pulse test current  $I_{T}$ .

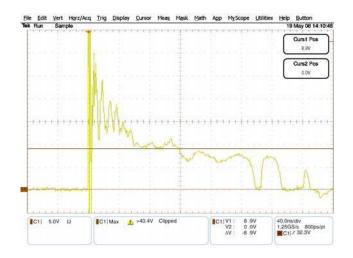


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

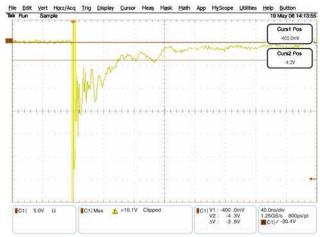
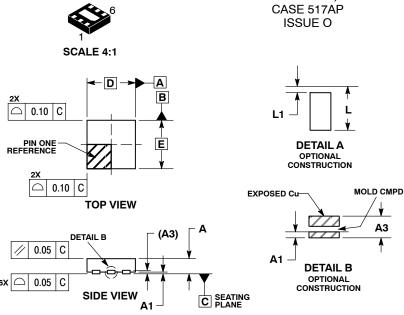
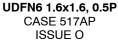


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

**DETAIL A** 

6X L





**DATE 26 OCT 2007** 

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER
  ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION & APPLIES TO PLATED TERMINAL
  AND IS MEASURED BETWEEN 0.15 AND
- 0.30 mm FROM TERMINAL. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00 0.05		
A3	0.13 REF		
b	0.20	0.30	
D	1.60 BSC		
E	1.60 BSC		
е	0.50 BSC		
D2	1.10	1.30	
E2	0.45	0.65	
K	0.20		
L	0.20	0.40	
L1	0.00	0.15	

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

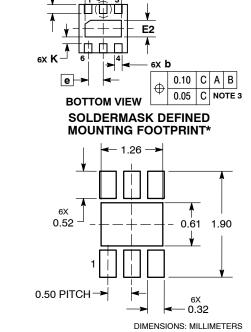
M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.



D2

\*For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	6 PIN UDFN, 1.6X1.6, 0.5P		PAGE 1 OF 1	

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